



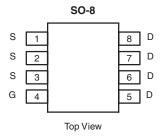
N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)		
30	0.012 at V _{GS} = 10 V	± 11		
	0.020 at V _{GS} = 4.5 V	± 9		

FEATURES

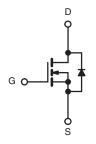
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- High-Efficiency PWM Optimized
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4890DY-T1-E3 (Lead (Pb)-free)

Si4890DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise no	oted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	± 25	V	
Opening David Opening (T., 450,00) a b	T _A = 25 °C	- I _D	± 11		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C		± 9	Δ.	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	± 50	Α	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	2.3	1	
Mariana Barray Disabati and b	T _A = 25 °C	P _D	2.5	w	
Maximum Power Dissipation ^{a, b}	T _A = 70 °C	' D	1.6	[
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Manianum lungtion to Ambient (MACCET)	t ≤ 10 s	R_{thJA}		50	°C/W	
Maximum Junction-to-Ambient (MOSFET) ^a	Steady State	' 'thJA	70		C/VV	

Notes

a. Surface Mounted on FR4 board.

b. $t \le 10 \text{ s}$.

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MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.8			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaga Dvain Current	1	V _{DS} = 24 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
	В	V _{GS} = 10 V, I _D = 11 A		0.0098	0.012	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 9 \text{ A}$		0.0164	0.020	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 11 A		21		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.3 A, V _{GS} = 0 V		0.71	1.1	V	
Dynamic ^b			•	•			
Total Gate Charge	Q_g			14.2	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5.0 \text{ V}, I_{D} = 11 \text{ A}$		3.3		nC	
Gate-Drain Charge	Q_{gd}			6.6			
Turn-On Delay Time	t _{d(on)}			13	20		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		8.5	15		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		35	53	ns	
Fall Time	t _f			17	26	1	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.3 A, dI/dt = 100 A/μs		35	70		

Notes:

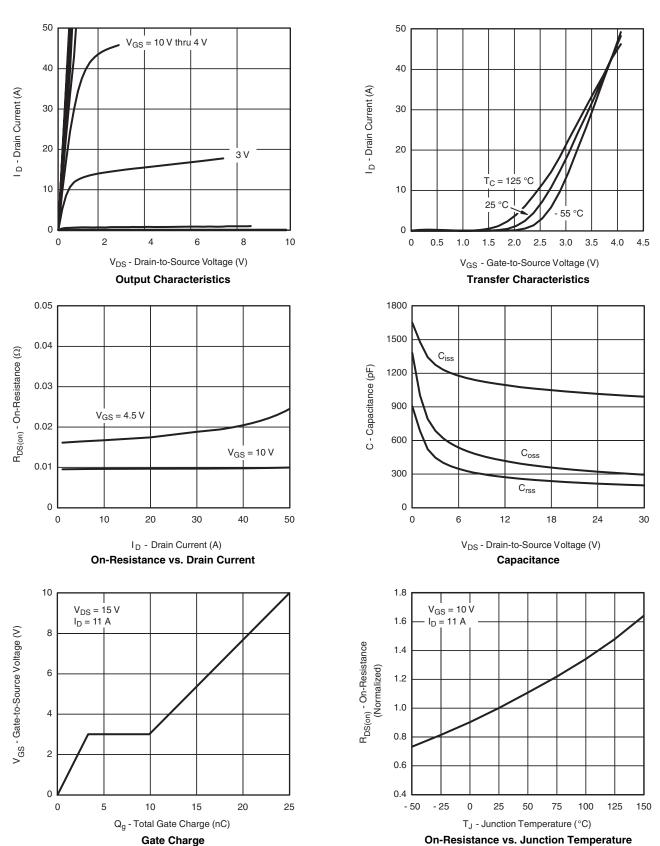
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



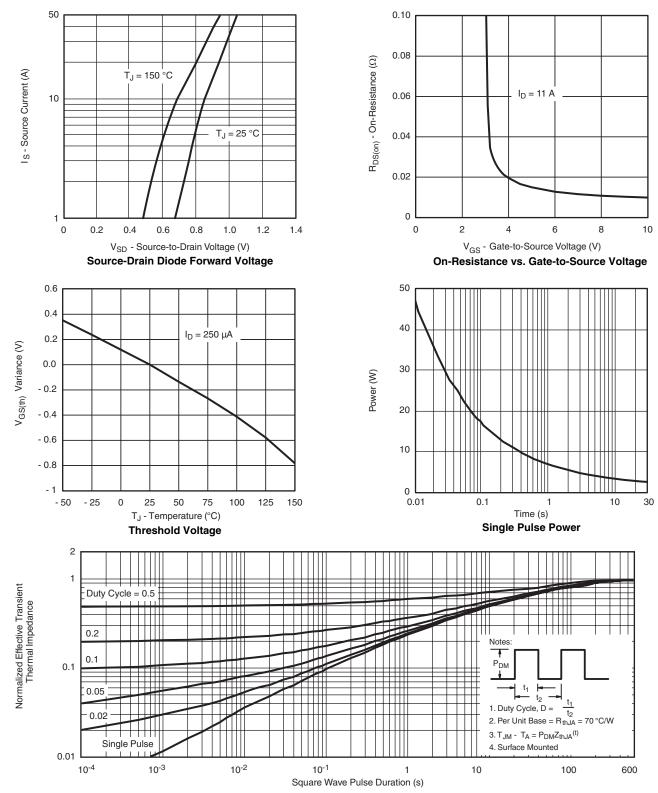
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg270855.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
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DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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